

### Abstract

An object is to improve soft error resistance of the memory cell of an SRAM without increasing its chip size. In deep through-holes formed by perforating a silicon oxide film, a silicon nitride film and a silicon oxide film, a capacitor element having a TiN film as a lower electrode, a silicon nitride film as an insulator and a TiN film as an upper electrode. This capacitor element is connected between a storage node and a supply voltage line, between a storage node and a reference voltage line, or between storage nodes of the memory cell of the SRAM.